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			Application Number	Not Yet Assigned	
			Filing Date		
			First Named Inventor	Leonard Forbes	
			Group Art Unit	N/A	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	2	Attorney Docket Number	M4065.0381/P381

09/808114
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U.S. PATENT DOCUMENTS						
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		Number	Kind Code ² (if known)			

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		Office ³	Number ⁴	Kind Code ⁵ (if known)				

Examiner Signature	Kevin Quinto	Date Considered	11/27/02
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72	A ✓	S. Tiwari, et al., "Straddle Gate Transistors: High I _{on} /I _{off} Transistors at Short Gate Lengths" IBM Research Division.	
	B ✓	W. Long, et al., "Dual-Material Gate (DMG) Field Effect Transistor."	
	C ✓	N. R. Rueger, et al. "Selective Etching of SiO ₂ Over Polycrystalline Silicon Using CHF ₃ in an Inductively Coupled Plasma Reactor."	
	D ✓	S. Vallon, et al., "Polysilicon-germanium Gate Patterning Studies in a High Density Plasma Helicon Source", J. Vac. Sci. Technol. A 15(4), Jul/Aug 1997.	
	E ✓	P. Patel, et al., "Low Temperature VUV Enhanced Growth of Thin Silicon Dioxide Films" Applied Surface Science 46 (1990) 352-356.	
	F ✓	W. Shindo, et al., "Low-Temperature Large-Grain Poly-Si Direct Deposition by Microwave Plasma Enhanced Chemical Vapor Deposition Using SiH ₄ /Xe", J. Vac. Sci. Technol. A 17(5), Sep/Oct 1999.	
	G ✓	R. Nozawa, et al., "Low Temperature Polycrystalline Silicon Film Formation With and Without Charged Species in an Electron Cyclotron Resonance SiH ₄ /H ₂ Plasma-Enhanced Chemical Vapor Deposition", J. Vac. Sci. Technol. A 17(5), Sep/Oct 1999.	
	H ✓	C. Saha, et al., "Ion Assisted Growth and Characterization of Polycrystalline Silicon and Silicon-Germanium Films" (visited Nov. 18, 1999) < http://www.dialogselect.com/tech/cgi/pres >.	
	I	D. Landheer, et al., "Formation of High-Quality Silicon Dioxide Films by Electron Cyclotron Resonance Plasma Oxidation and Plasma-Enhanced Chemical Vapour Deposition" (visited Oct. 21, 1999) < http://www.dialogselect.com/tech/cgi/pres >.	
	J	K. Usami, et al., "Thin Si Oxide Films for MIS Tunnel Emitter by Hollow Cathode Enhanced Plasma Oxidation" (visited Oct. 21, 1999) < http://www.dialogselect.com/tech/cgi/pres >.	
	K	K.C. Saraswat, et al. "A Low Temperature Polycrystalline SiGe CMOS TFT Technology for Large Area AMLCD Drivers" (visited 11/18/99) < http://www.dialogselect.com/tech/cgi/pres >.	

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